

## Title (en)

Process for producing silicon oxide films from organoaminosilane precursors

## Title (de)

Verfahren zur Herstellung von Siliziumoxidschichten aus Organoaminosilanvorläuferverbindungen

## Title (fr)

Procédé pour la fabrication de films d'oxyde de silicium à partir de précurseurs organoaminosilane

## Publication

**EP 1860690 B1 20181024 (EN)**

## Application

**EP 07108782 A 20070523**

## Priority

US 43955406 A 20060523

## Abstract (en)

[origin: EP1860690A2] A silicon oxide layer is deposited on a substrate by chemical vapor deposition (CVD) by reacting an organoaminosilane precursor, selected from specified categories, with an oxidizing agent under conditions for the formation of a silicon oxide film. Diisopropylaminosilane is the preferred organoaminosilane precursor for the formation of the silicon oxide film.

## IPC 8 full level

**H01L 21/316** (2006.01); **C23C 16/40** (2006.01)

## CPC (source: EP KR US)

**C07F 7/10** (2013.01 - KR); **C23C 16/402** (2013.01 - EP KR US); **C23C 16/42** (2013.01 - KR); **H01L 21/02126** (2013.01 - EP KR US); **H01L 21/02219** (2013.01 - EP KR US); **H01L 21/02271** (2013.01 - EP KR US); **H01L 21/3145** (2013.01 - US); **H01L 21/31608** (2013.01 - US); **H01L 21/31633** (2013.01 - US)

## Citation (examination)

- JP H06132276 A 19940513 - KAWASAKI STEEL CO
- WO 2006097525 A2 20060921 - AIR LIQUIDE [FR], et al
- EP 1724373 A1 20061122 - AIR PROD & CHEM [US]

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EP2484803A1; EP2484801A1; EP2484802A1; EP2650399A3; WO2012107138A1; WO2021050368A1; US9460912B2; US10242864B2

## Designated contracting state (EPC)

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## DOCDB simple family (publication)

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## DOCDB simple family (application)

**EP 07108782 A 20070523**; CN 200710104246 A 20070523; CN 201310103494 A 20070523; CN 201310137899 A 20070523; EP 12190450 A 20070523; EP 12190454 A 20070523; JP 2007135666 A 20070522; JP 2010249926 A 20101108; JP 2011082821 A 20110404; JP 2013243373 A 20131125; JP 2014018171 A 20140203; JP 2015023549 A 20150209; JP 2015038698 A 20150227; JP 2015106450 A 20150526; JP 2017158744 A 20170821; KR 20070047512 A 20070516; KR 20090015985 A 20090225; KR 20090112859 A 20091120; KR 20120075731 A 20120711; KR 20130003048 A 20130110; KR 20130130985 A 20131031; TW 96117653 A 20070517; TW 99133386 A 20070517; US 43955406 A 20060523